

In the Claims:

1. (currently amended) A light emitting device of a II-VI group compound semiconductor formed on a compound semiconductor substrate and having an active layer between an n-type cladding layer and a p-type cladding layer, comprising

[[*]] an i-type semiconductor barrier layer having a band gap larger than a band gap of said p-type cladding layer, provided between said active layer and said p-type cladding layer.

2. (withdrawn) The semiconductor light emitting device according to claim 1, wherein

said light emitting device of the II-VI group compound is a ZnSe based light emitting device;

said n-type cladding layer is an n-type $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$ ($0 < x < 1$, $0 < y < 1$) layer; and

said p-type cladding layer is a p-type $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$ ($0 < x < 1$, $0 < y < 1$) layer.

3. (original) The semiconductor light emitting device according to claim 1, wherein

magnitude of the band gap of said barrier layer is larger by 0.025 eV to 0.5 eV than the band gap of said p-type cladding layer.

4. (previously presented) The semiconductor light emitting device according to claim 1, wherein

in the band gap of said barrier layer, energy of valence band is approximately the same as or higher than that of said p-type cladding layer, and energy of conductive band is larger than that of said p-type cladding layer.

5. (original) The semiconductor light emitting device according to claim 1, wherein

said barrier layer is of a II-VI group compound semiconductor containing Be.

6. (original) The semiconductor light emitting device according to claim 5, wherein

said barrier layer is of $\text{Zn}_{1-x-y}\text{Mg}_x\text{Be}_y\text{Se}$ ($0 \leq x + y \leq 1$, $0 < x$, $0 < y$).

7. (withdrawn) The semiconductor light emitting device according to claim 1, wherein

said barrier layer is of $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$.

8. (withdrawn) The semiconductor light emitting device according to claim 1, comprising

a semiconductor trap layer having a band gap smaller than a band gap of said p-type cladding layer, provided between said barrier layer and said p-type cladding layer.

1 **9.** (withdrawn) The semiconductor light emitting device
2 according to claim 8, having a multi-stacked structure in
3 which a plurality of double-layer-structure of said barrier
4 layer and said trap layer are stacked.

1 **10.** (withdrawn) The semiconductor light emitting device
2 according to claim 8, wherein
3 said trap layer is of $\text{ZnS}_x\text{Se}_{1-x}$ ($0 \leq x \leq 0.1$).

1 **11.** (original) The semiconductor light emitting device
2 according to claim 1, wherein
3 said p-type cladding layer is formed of
4 $(\text{Zn}_{1-x}\text{Cd}_x\text{S})_{1-z}(\text{MgS}_{1-y}\text{Se}_y)_z$ (where x, y, z satisfy $0 < x \leq 1$,
5 $0 \leq y \leq 1$, $0 \leq z < 1$).

1 **12.** (original) The semiconductor light emitting device
2 according to claim 1, wherein
3 thickness of said barrier layer is at least 5 nm and
4 at most thickness of said active layer.

1 **13.** (original) The semiconductor light emitting device
2 according to claim 1, wherein
3 an n-type ZnSe single crystal substrate is used as
4 said compound semiconductor substrate.

1 **14.** (original) The semiconductor light emitting device
2 according to claim 1, wherein

3 an n-type GaAs single crystal substrate is used as
4 said compound semiconductor substrate.

1 **15.** (original) The semiconductor light emitting device
2 according to claim 1, wherein

3 in a stacked structure including said compound
4 semiconductor substrate constituting said ZnSe based light
5 emitting device, deviation between a peak of X-ray
6 diffraction of a plane orientation used as an index of
7 distortion from said substrate and a peak of X-ray
8 diffraction of said plane orientation from said stacked
9 structure is at most 1000 seconds.

Claims 16 to 22 (cancelled).

1 **23.** (new) The semiconductor light emitting device according to
2 claim 1, wherein said barrier layer is a single monolayer
3 interposed between said active layer and said p-type
4 cladding layer.

1 **24.** (new) The semiconductor light emitting device according to
2 claim 1, wherein said barrier layer is disposed directly on
3 said active layer.

1 **25.** (new) The semiconductor light emitting device according to
2 claim 1, wherein said p-type cladding layer is disposed
3 directly on said barrier layer.